



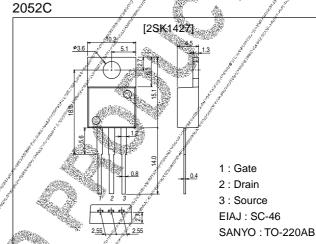
Ultrahigh-Speed Switching Applications

Features

- · Low ON-state resistance.
- · Ultrahigh-speed switching.
- · Converters.

Package Dimensions

unit:mm



Specifications

Absolute Maximum Ratings at Ta = 25°C

Parameter	Symbol	Ratings	Unit
Drain-to-Source Voltage	V _{DS} \$	100	V
Gate-to-Source Voltage	VGSS	±20	V
Drain Current (DC)	/,6	10	Α
Drain Current (Pulse)	/ I _{DP} PW≥10us, duty cycle≤1%	40	Α
Allowable Power Dissipation	TC=25°C	40	W
		1.75	W
Channel Temperature	/ Ach	150	°C
Storage Temperature	// Estg //	-55 to +150	°C

Electrical Characteristics at Ta = 25°C

Parameter	Symbol	Conditions	Ratings			Unit
raidiffeter			min	typ	max	Offic
Drain-to-Source Breakdown Voltage	V(BR)DSS	ID=1mA, V _{GS} =0	100			V
Zero-Gate Voltage Drain/Current	IDSS	V _{DS} =100V, V _{GS} =0			100	μA
Gate-to-Source Leakage Current	I _{G\$S} ,	$V_{GS}=\pm20V$, $V_{DS}=0$			±100	nA
Cutoff Voltage	V@S(off)	$V_{DS}=10V$, $I_{D}=1mA$	1.5		2.5	V
Forward Transfer Admittance	/ yfs	V _{DS} =10V, I _D =6A	5.0	8.0		S
Static Drain-to-Source ON-State Resistance	RDS(on)	I _D =6A, V _{GS} =10V		0.12	0.16	Ω

(Note) Be careful in handling the 25k 1427 because it has no protection diode between gate and source.

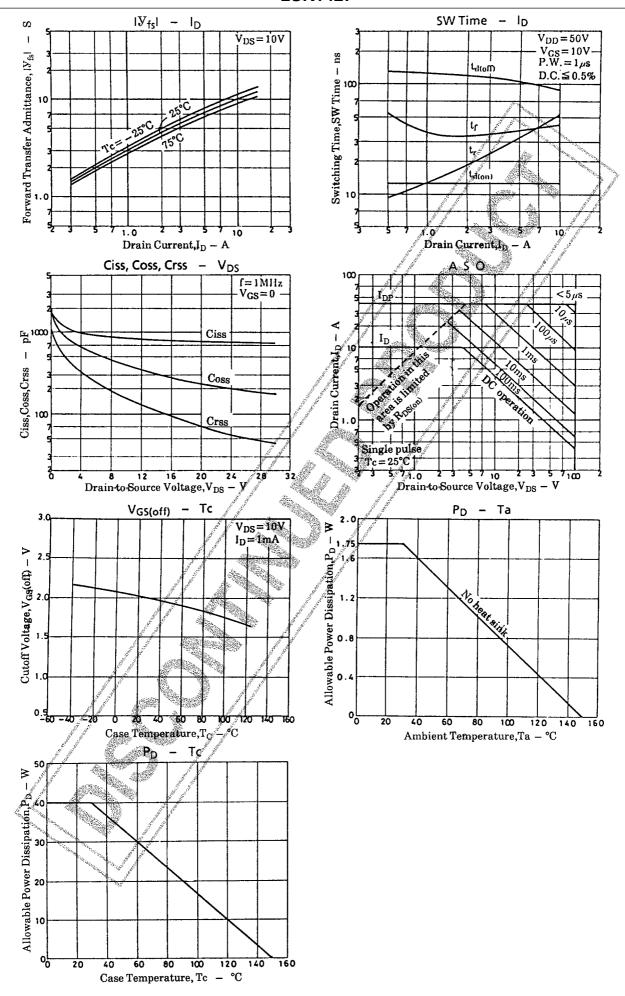
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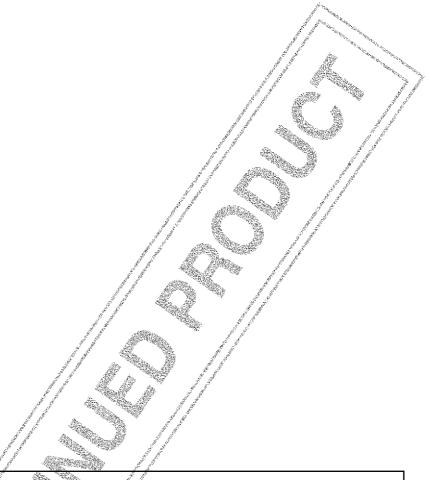
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Parameter	Symbol Conditions	Conditions		Ratings			Unit
r atameter			min	typ	max	Offic	
Input Capacitance	Ciss	V _{DS} =20V, f=1MHz			750		pF
Output Capacitance	Coss	V _{DS} =20V, f=1MHz			230		pF
Reverse Transfer Capacitance	Crss	V _{DS} =20V, f=1MHz		1	70		pF
Turn-ON Delay Time	t _d (on)	I_{D} =6A, V_{GS} =10V, V_{DD} =50V, R_{GS} =50 Ω		A STATE OF THE PARTY OF THE PAR	12		ns
Rise Time	t _r	I_{D} =6A, V_{GS} =10V, V_{DD} =50V, R_{GS} =50 Ω	J.	F F	.38	Carly Str.	ns
Turn-OFF Delay Time	td(off)	I_{D} =6A, V_{GS} =10V, V_{DD} =50V, R_{GS} =50 Ω	ge ^{zer} l	Y A	100	Parket Mary Control of the Control o	ns
Fall Time	t _f	I_{D} =6A, V_{GS} =10V, V_{DD} =50V, R_{GS} =50 Ω	May May	40	40	Carlo Maria	ns
Diode Forward Voltage	V _{SD}	I _S =10A, V _{GS} =0	3 4	1 market and		1.8	<i></i> V

Switching Time Test Circuit V_{DD} 50V P.W. =1 #8 D.C. ≦0.5% 8.30 6A VGS Vout AGS 500 ID - VDS - VGS ID 20 $V_{DS} = 10V$ **5**γ Drain Current, ID - A Drain Current, ID 4V 3.5V ₹3V 2 6 8 Drain-to-Source Voltage, V_{DS} – V 10 Gate-to-Source Voltage, $V_{GS} - V$ RDS(on) -Vigs RDS(on) - Tc 280 400 ШЛ Tc = 25°C $I_D = 6\Lambda$ $V_{GS} = 10V$ $m\Omega$ $I_D = 6\Lambda$ 350 Static Drain-to-Source ON- State Resistance, Roscon. – Static Drain-to-Source ON- State Resistance, R_{DS(on)} – ٥Į 0 -40 -20 20 40 60 80 100 120 140 160 Gate-to-Source Voltage, $V_{GS} - V$ Case Temperature, $T_C - {}^{\circ}C$





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